

Single P-Channel MOSFET

DESCRIPTION

SMC3347 is the P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced trench technology devices are well suited for high efficiency fast switching applications, low in-line power loss needed in small outline surface mount package.

PART NUMBER INFORMATION

SMC 3347 SN - TR G
 a b c d e

- a : Company name.
- b : Product Serial number.
- c : Package code SN: SOT-23
- d : Handling code TR: Tape&Reel
- e : Green produce code G: *RoHS Compliant*

FEATURES

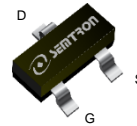
$V_{DS} = -30V$, $I_D = -4.1A$

$R_{DS(ON)}=44m\Omega(Typ.)@V_{GS}=-10V$
 $R_{DS(ON)}=50m\Omega(Typ.)@V_{GS}=-4.5V$
 $R_{DS(ON)}=65m\Omega(Typ.)@V_{GS}=-2.5V$

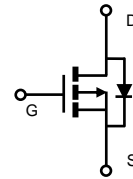
- ◆ Fast switch
- ◆ 2.5V Low gate drive applications

APPLICATIONS

- ◆ Portable Equipment
- ◆ Power Management
- ◆ Load Switch



SOT-23



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ Unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A=25^\circ C$	-4.1
		$T_A=70^\circ C$	-3.3
I_{DM}	Pulsed Drain Current ^A	-16.4	A
P_D	Power Dissipation ^B	$T_A=25^\circ C$	1.3
		$T_A=70^\circ C$	0.8
T_J	Operation Junction Temperature	-55/150	$^\circ C$
T_{STG}	Storage Temperature Range	-55/150	$^\circ C$

THERMAL RESISTANCE

Symbol	Parameter	Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ^B	$t \leq 10s$	95	$^\circ C/W$
	Thermal Resistance Junction to Ambient ^{BC}	Steady-State	130	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

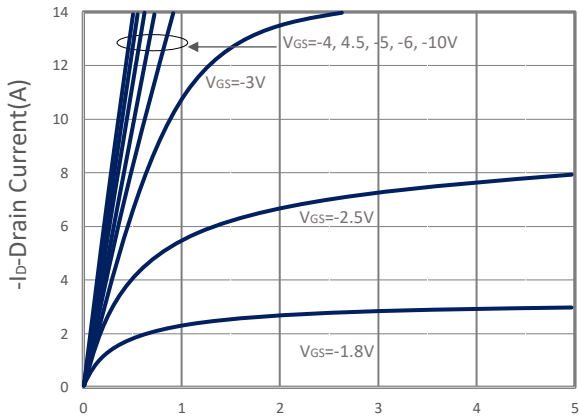
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μ A	-0.5	-0.7	-1	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = \pm 12V			\pm 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V, T _J =25 $^\circ$ C			-1	μ A
		V _{DS} =-24V, V _{GS} =0V, T _J =75 $^\circ$ C			-10	
R _{DS(ON)}	Drain-source On-Resistance	V _{GS} =-10V, I _D =-4.1A		44	48	m Ω
		V _{GS} =-4.5V, I _D =-3.2A		50	58	
		V _{GS} =-2.5V, I _D =-2.2A		65	78	
G _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-4.1A		5.9		S
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Continuous Source Current				-4.1	A
Dynamic and Switching Parameters						
Q _g (10V)	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _D =-4A		24.6	34.4	nC
Q _g (4.5V)	Total Gate Charge			12	16.8	
Q _{gs}	Gate-Source Charge			1.75	2.5	
Q _{gd}	Gate-Drain Charge			3.1	4.3	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		905		pF
C _{oss}	Output Capacitance			75		
C _{rss}	Reverse Transfer Capacitance			67		
t _{d(on)}	Turn-On Time	V _{DD} =-15V, V _{GEN} =-10V, R _G =3 Ω , I _D =-1A		6.2	12	nS
t _r				27	51	
t _{d(off)}	Turn-Off Time			46.5	88	
t _f				29	55	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

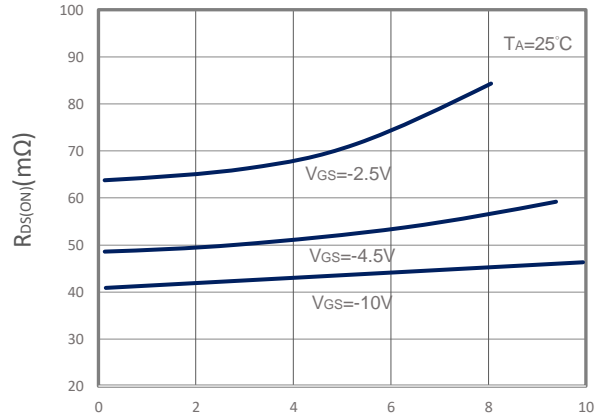
- Pulsed width limited by maximum junction temperature, T_{J(MAX)}=150 $^\circ$ C.
- Measure the value in a still air environment at T_A=25 $^\circ$ C, using an installation mounted on a 1 in2 FR-4 board, maximum junction temperature T_{J(MAX)}=150 $^\circ$ C.
- T_{J(MAX)}=150 $^\circ$ C, using junction-to-case thermal resistance (R_{θJC}) is more useful in additional heat sinking is used.

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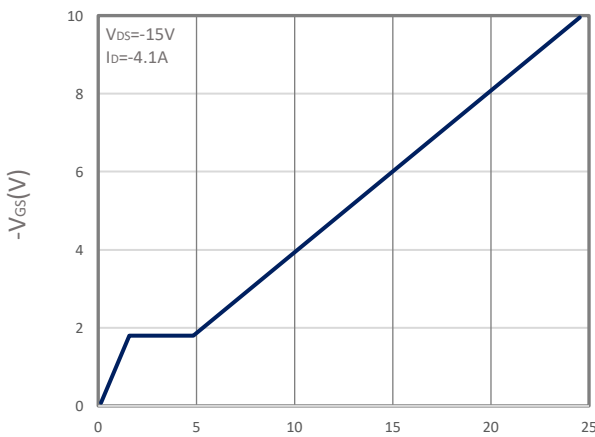
TYPICAL CHARACTERISTICS



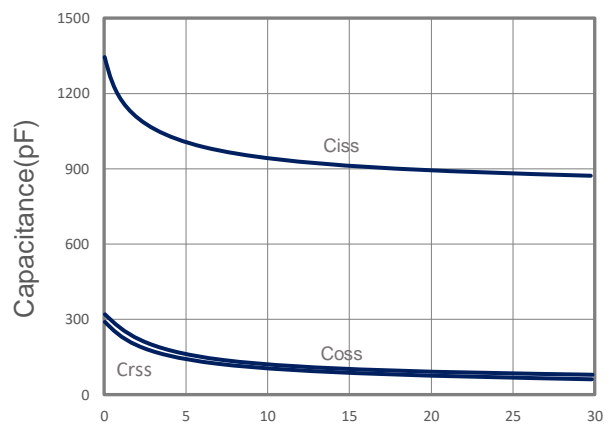
Output Characteristics



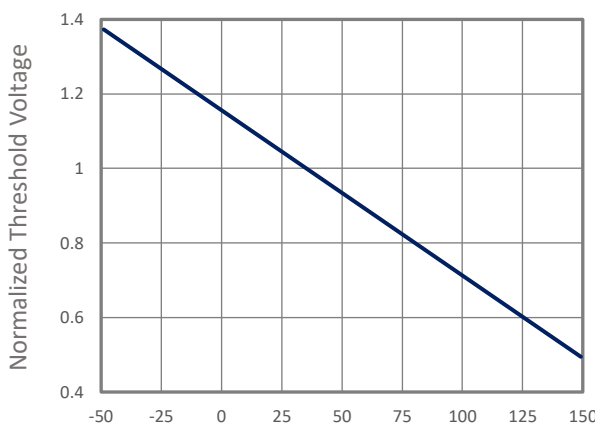
Drain-Source On Resistance



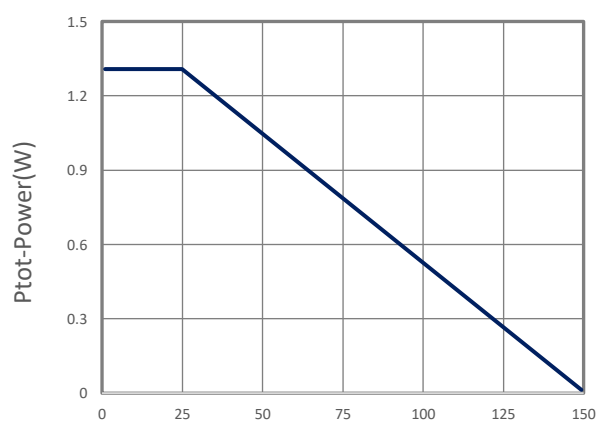
Gate Charge



Capacitance

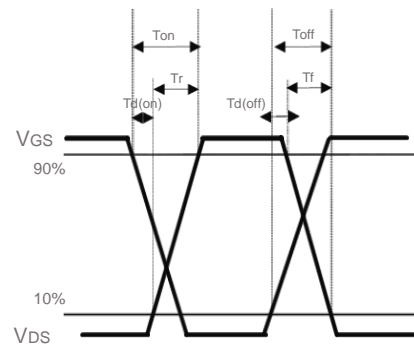
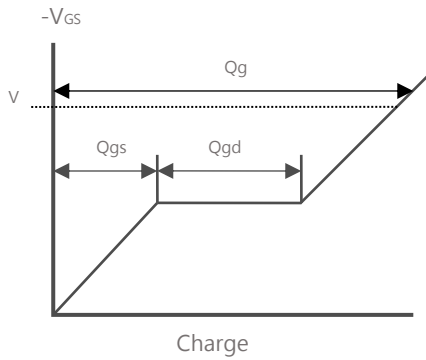
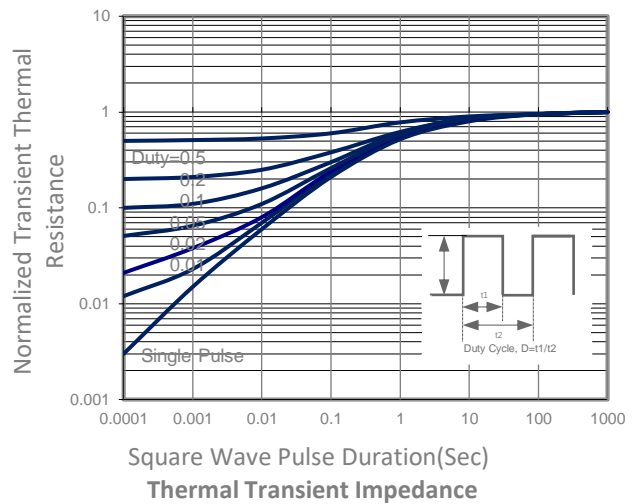
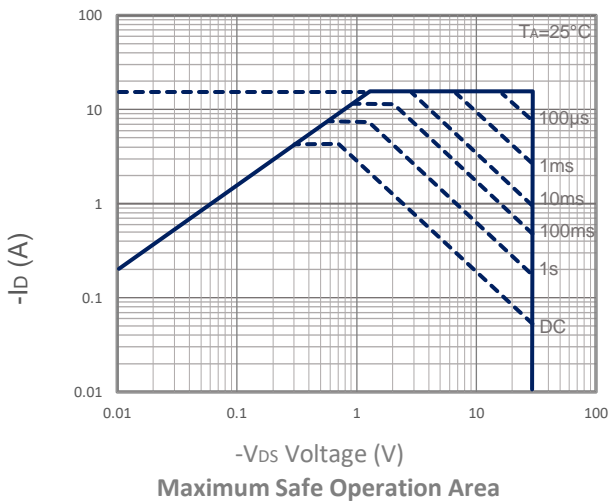
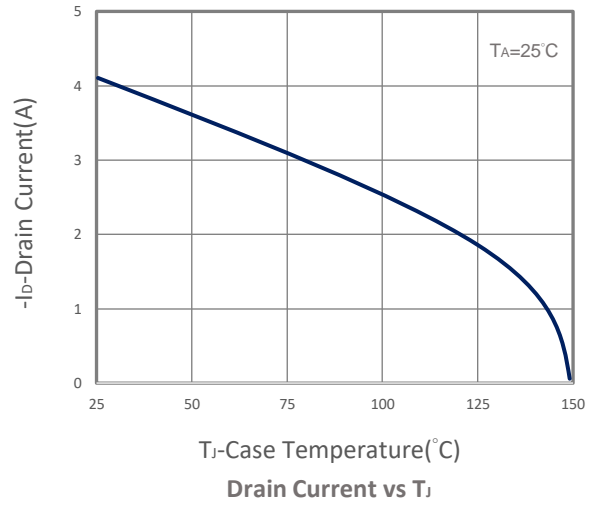
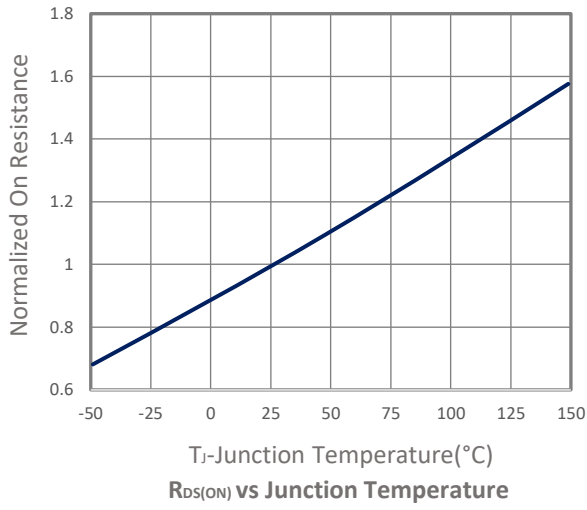


Gate Threshold Voltage

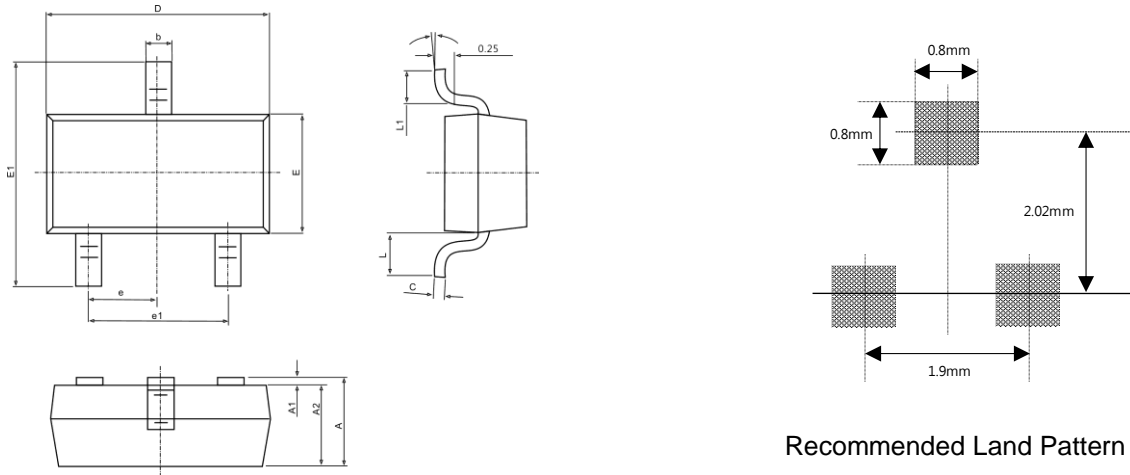


Power Dissipation

TYPICAL CHARACTERISTICS



SOT-23 PACKAGE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°